

HSM107S

Silicon Schottky Barrier Diode for System Protection

HITACHI

ADE-208-058F(Z)

Rev 6

Sep. 1998

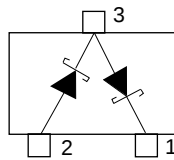
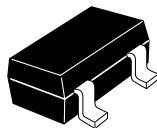
Features

- Low V_F and high efficiency.
- HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM107S	C5	MPAK

Outline



(Top View)

- 1 Cathode 2
- 2 Anode 1
- 3 Cathode 1
Anode 2

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	8	V
Peak forward current	I_{FM}	0.1	A
Non-Repetitive Peak forward surge current	I_{FSM}^{*1}	0.5	A
Average forward current	I_O	50	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Notes: 1. Square wave, 10ms

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	8	—	—	—	$I_R = 1.0\text{ mA}$
Reverse current	I_R	—	—	30	μA	$V_R = 5\text{ V}$
Forward voltage	V_F	—	—	0.3	V	$I_F = 10\text{ mA}$
ESD Capability ^{*1}	—	100	—	—	V	C=200pF, Both forward and reverse direction 1 pulse

Notes: 1. Failure Criterion ; $I_R \geq 60\mu\text{A}$ at $V_R=5\text{V}$

Main Characteristic

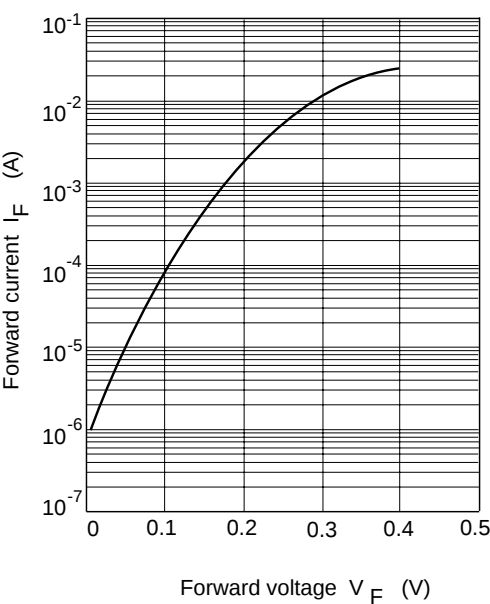


Fig.1 Forward current Vs. Forward voltage

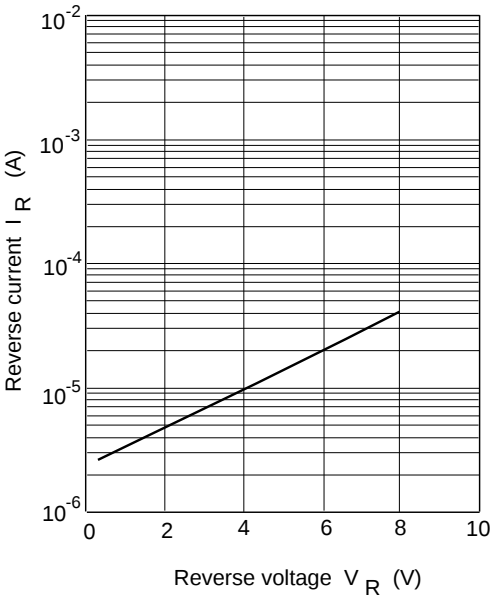


Fig.2 Reverse current Vs. Reverse voltage

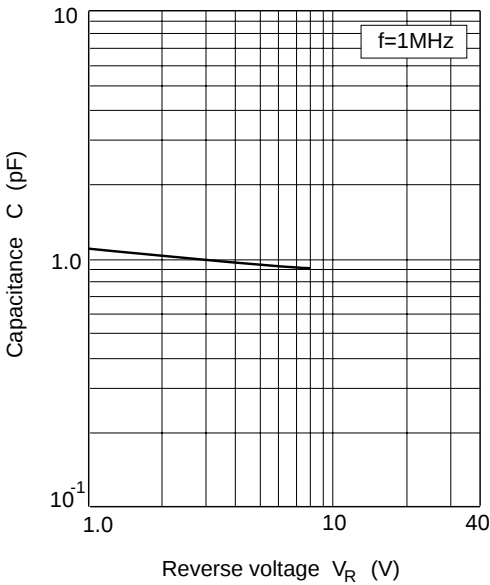
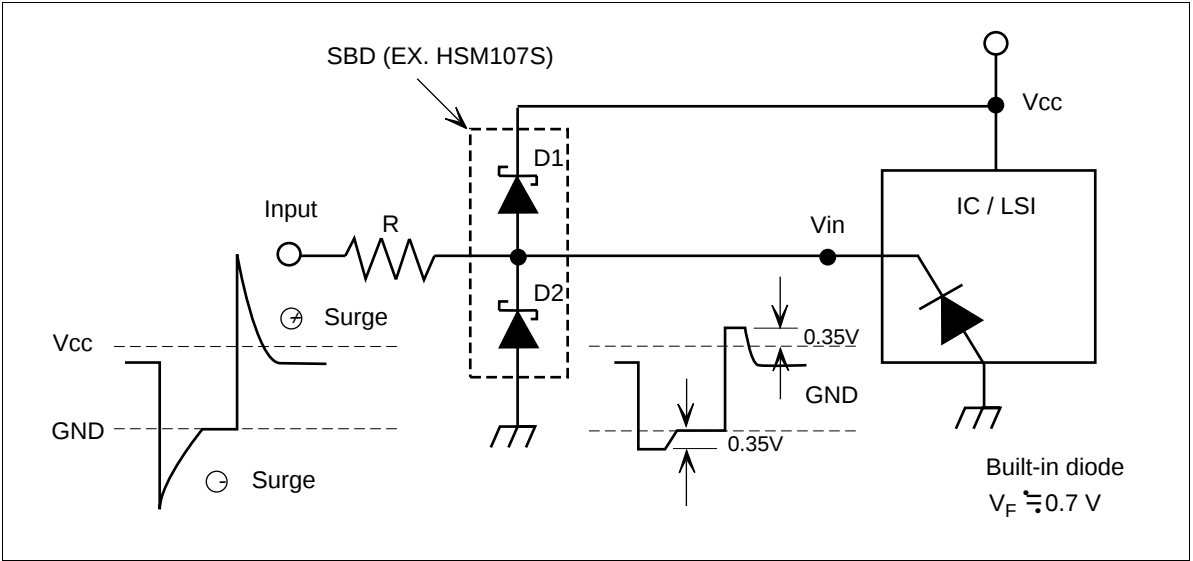


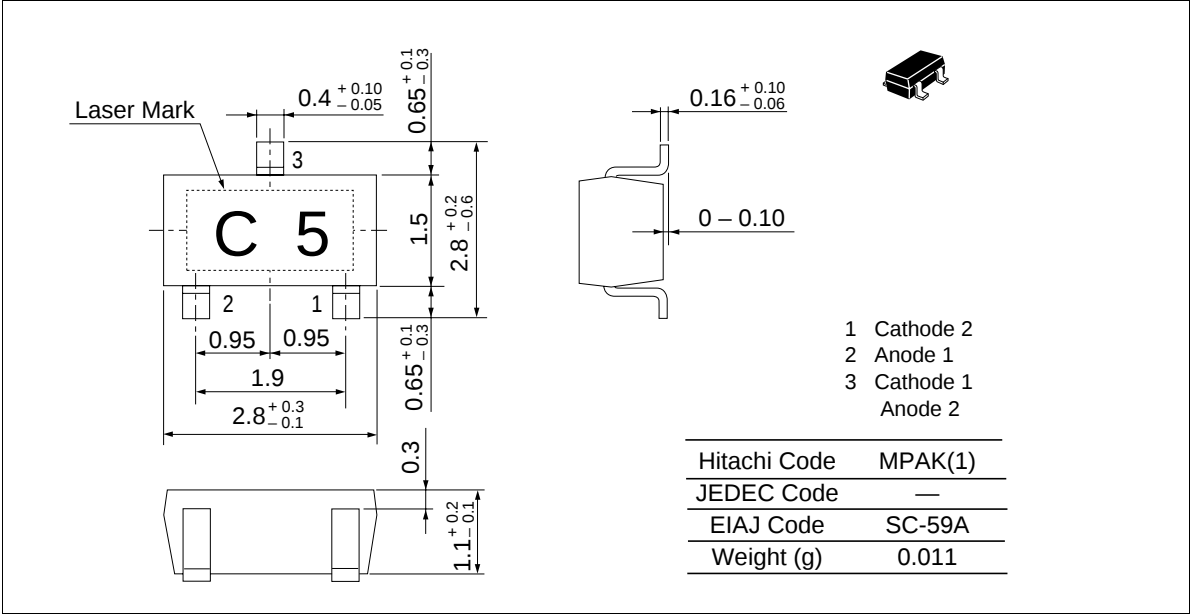
Fig.3 Capacitance Vs. Reverse voltage

Example of application circuit



Package Dimensions

Unit : mm



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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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